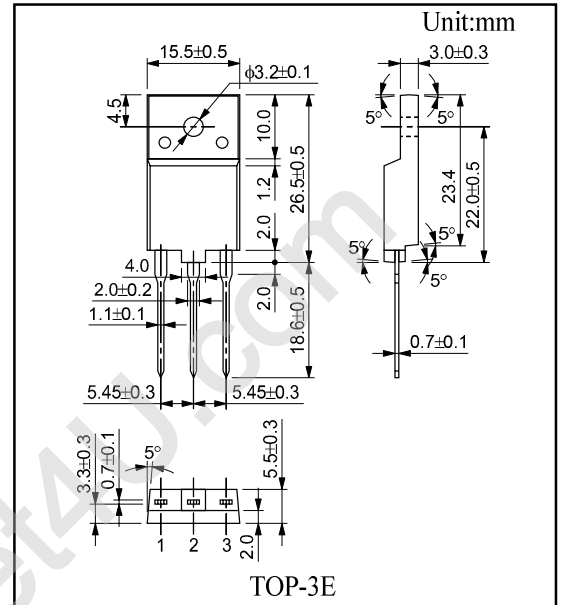


2SC5572

■ Absolute Maximum Ratings

| Parameter | Symbol | Rating | Unit |
|------------------------------|--------|-------------|------|
| Collector to base voltage | VCBO | 1500 | V |
| Collector to emitter voltage | VCES | 1500 | V |
| Emitter to base voltage | VEBO | 7 | V |
| Peak collector current | ICP | 12*3 | A |
| Collector current | IC | 6 | A |
| Base current | IB | 3 | A |
| Collector power dissipation | PC | 40*1 3*2 | W |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | | -55 to +150 | °C |



*1)TC=25°C ,*2)Ta=25°C(Without heat sink)

*3)Non-repetitive peak collector current.

■ Electrical Characteristics(TC=25°C)

| Parameter | Symbol | Conditions | min | typ | max | Unit |
|---|----------------------|---|-----|-----|-----|------|
| Collector cutoff current | ICBO | V _{CB} =1000V,I _E =0 | - | - | 50 | μA |
| | ICBO | V _{CB} =1500V,I _E =0 | - | - | 1 | mA |
| Emitter to base voltage | VEBO | I _E =500mA,I _C =0 | 7 | - | - | V |
| Forward current transfer ratio | f _{FE} | V _{CE} =5V,I _C =4A | 5 | - | 9 | |
| Collector to emitter saturation voltage | V _{CE(sat)} | I _C =4A,I _B =0.8A | - | - | 3 | V |
| Base to emitter saturation voltage | V _{BE(sat)} | I _C =4A,I _B =0.8A | - | - | 1.5 | V |
| Transition frequency | f _T | V _{CE} =10V,I _C =0.1A,f=0.5MHz | - | 3 | - | MHz |
| Storage time | T _{stg} | I _C =4A,I _{B1} =0.8A,I _{B2} =-1.6A | - | - | 5.0 | μs |
| Fall time | T _f | I _C =4A,I _{B1} =0.8A,I _{B2} =-1.6A | - | - | 0.5 | μs |
| Diode characteristics | V _F | I _F =4A | - | - | -2 | V |